

Data Sheet

FEATURES

Latch-up proof

8 kV human body model (HBM) ESD rating
Low on resistance (<10 Ω)
±9 V to ±22 V dual-supply operation
9 V to 40 V single-supply operation
48 V supply maximum ratings
Fully specified at ±15 V, ±20 V, +12 V, and +36 V
V_{SS} to V_{DD} analog signal range

APPLICATIONS

Relay replacement Automatic test equipment Data acquisition Instrumentation Avionics Audio and video switching Communication systems

GENERAL DESCRIPTION

The ADG5412/ADG5413 contain four independent single-pole/ single-throw (SPST) switches. The ADG5412 switches turn on with Logic 1. The ADG5413 has two switches with digital control logic similar to that of the ADG5412; however, the logic is inverted on the other two switches. Each switch conducts equally well in both directions when on, and each switch has an input signal range that extends to the supplies. In the off condition, signal levels up to the supplies are blocked.

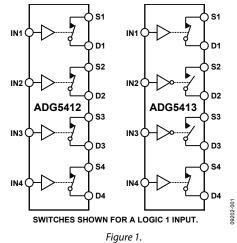
The ADG5412 and ADG5413 do not have a V_L pin. The digital inputs are compatible with 3 V logic inputs over the full operating supply range.

The on-resistance profile is very flat over the full analog input range, which ensures good linearity and low distortion when switching audio signals. High switching speed also makes the devices suitable for video signal switching. The ADG5413 exhibits break-before-make switching action for use in multiplexer applications.

High Voltage Latch-Up Proof, Quad SPST Switches

ADG5412/ADG5413

FUNCTIONAL BLOCK DIAGRAMS



PRODUCT HIGHLIGHTS

- 1. Trench isolation guards against latch-up. A dielectric trench separates the P and N channel transistors thereby preventing latch-up even under severe overvoltage conditions.
- 2. Low Ron.
- 3. Dual-supply operation. For applications where the analog signal is bipolar, the ADG5412/ADG5413 can be operated from dual supplies up to ±22 V.
- 4. Single-supply operation. For applications where the analog signal is unipolar, the ADG5412/ADG5413 can be operated from a single rail power supply up to 40 V.
- 5. 3 V logic compatible digital inputs: $V_{INH} = 2.0$ V, $V_{INL} = 0.8$ V.
- 6. No V_L logic power supply required.

Rev. D

Document Feedback

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REVISION HISTORY

11/2017-Rev. C to Rev. D

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5/2016—Rev. B to Rev. C

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9/2015—Rev. A to Rev. B

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6/2011-Rev. 0 to Rev. A

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7/2010—Revision 0: Initial Version

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SPECIFICATIONS

±15 V DUAL SUPPLY

 V_{DD} = +15 V \pm 10%, V_{SS} = –15 V \pm 10%, GND = 0 V, unless otherwise noted.

Table 1.

Parameter	+25°C	–40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			V _{DD} to V _{SS}	V	
On Resistance, R _{on}	9.8			Ωtyp	$V_s = \pm 10 V$, $I_s = -10 mA$; see Figure 24
	11	14	16	Ωmax	$V_{DD} = +13.5 V$, $V_{SS} = -13.5 V$
On-Resistance Match Between Channels, ΔR_{ON}	0.35			Ωtyp	$V_{s} = \pm 10 V$, $I_{s} = -10 mA$
	0.7	0.9	1.1	Ωmax	
On-Resistance Flatness, R _{FLAT (ON)}	1.2			Ωtyp	$V_s = \pm 10 V$, $I_s = -10 mA$
	1.6	2	2.2	Ωmax	
LEAKAGE CURRENTS					$V_{DD} = +16.5 V, V_{SS} = -16.5 V$
Source Off Leakage, I _s (Off)	±0.05			nA typ	$V_{s} = \pm 10 \text{ V}, V_{D} = \mp 10 \text{ V};$ see Figure 27
	±0.25	±0.75	±6	nA max	_
Drain Off Leakage, I_D (Off)	±0.05			nA typ	$V_S = \pm 10 \text{ V}, V_D = \mp 10 \text{ V};$ see Figure 27
	±0.25	±0.75	±6	nA max	
Channel On Leakage, I _D (On), I _s (On)	±0.1			nA typ	$V_s = V_D = \pm 10 V$; see Figure 23
-	±0.4	±2	±12	nA max	
DIGITAL INPUTS					
Input High Voltage, V _{INH}			2.0	V min	
Input Low Voltage, VINL			0.8	V max	
Input Current, I _{INL} or I _{INH}	0.002			μA typ	$V_{IN} = V_{GND} \text{ or } V_{DD}$
			±0.1	µA max	
Digital Input Capacitance, C _{IN}	2.5			pF typ	
DYNAMIC CHARACTERISTICS ¹					
ton	170			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	202	236	262	ns max	$V_s = 10 V$; see Figure 31
toff	120			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	145	170	182	ns max	$V_s = 10 V$; see Figure 31
Break-Before-Make Time Delay, t _D (ADG5413 Only)	15			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
			6	ns min	$V_{s1} = V_{s2} = 10 V$; see Figure 30
Charge Injection, Q _{INJ}	240			pC typ	$V_s = 0 V$, $R_s = 0 \Omega$, $C_L = 1 nF$; see Figure 32
Off Isolation	-78			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, f = 100 kHz; see Figure 26
Channel-to-Channel Crosstalk	-70			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 25
Total Harmonic Distortion + Noise	0.009			% typ	R_L = 1 kΩ, 15 V p-p, f = 20 Hz to 20 kHz; see Figure 28
-3 dB Bandwidth	167			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 29
Insertion Loss	-0.7			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 29
C _s (Off)	18			pF typ	$V_{s} = 0 V, f = 1 MHz$
C _D (Off)	18			pF typ	$V_{s} = 0 V, f = 1 MHz$
C _D (On), C _s (On)	60			pF typ	$V_{s} = 0 V, f = 1 MHz$

Parameter	+25°C -40°C to +85	°C -40°C to +125°C	Unit	Test Conditions/Comments
POWER REQUIREMENTS				$V_{DD} = +16.5 V$, $V_{SS} = -16.5 V$
l _{DD}	45		μA typ	Digital inputs = $0 V \text{ or } V_{DD}$
	55	70	μA max	
lss	0.001		μA typ	Digital inputs = $0 V \text{ or } V_{DD}$
		1	μA max	
V _{DD} /V _{ss}		±9/±22	V min/V max	GND = 0 V

¹ Guaranteed by design; not subject to production test.

±20 V DUAL SUPPLY

 V_{DD} = +20 V \pm 10%, V_{SS} = -20 V \pm 10%, GND = 0 V, unless otherwise noted.

Table 2.

Parameter	+25°C	–40°C to +85°C	–40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			V _{DD} to V _{ss}	V	
On Resistance, R _{ON}	9			Ωtyp	$V_s = \pm 15 V$, $I_s = -10 mA$; see Figure 24
	10	13	15	Ωmax	$V_{DD} = +18 V, V_{SS} = -18 V$
On-Resistance Match Between Channels, ΔR _{oN}	0.35			Ωtyp	$V_s = \pm 15 V$, $I_s = -10 mA$
	0.7	0.9	1.1	Ωmax	
On-Resistance Flatness, R _{FLAT (ON)}	1.5			Ωtyp	$V_{s} = \pm 15 V$, $I_{s} = -10 mA$
	1.8	2.2	2.5	Ωmax	
LEAKAGE CURRENTS					$V_{DD} = +22 V, V_{SS} = -22 V$
Source Off Leakage, Is (Off)	±0.05			nA typ	$V_s = \pm 15 V$, $V_D = \mp 15 V$; see Figure 27
	±0.25	±0.75	±6	nA max	
Drain Off Leakage, I_D (Off)	±0.05			nA typ	$V_s = \pm 15 V$, $V_D = \mp 15 V$; see Figure 27
	±0.25	±0.75	±6	nA max	
Channel On Leakage, $I_{\rm D}$ (On), $I_{\rm S}$ (On)	±0.1			nA typ	$V_s = V_D = \pm 15 V$; see Figure 23
	±0.4	±2	±12	nA max	
DIGITAL INPUTS					
Input High Voltage, VINH			2.0	V min	
Input Low Voltage, VINL			0.8	V max	
Input Current, IINL or IINH	0.002			μA typ	$V_{IN} = V_{GND} \text{ or } V_{DD}$
			±0.1	μA max	
Digital Input Capacitance, C _{IN}	2.5			pF typ	
DYNAMIC CHARACTERISTICS ¹					
ton	158			ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
	187	217	240	ns max	$V_s = 10 V$; see Figure 31
toff	110			ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
	138	154	170	ns max	$V_s = 10 V$; see Figure 31
Break-Before-Make Time Delay, t₀ (ADG5413 Only)	12			ns typ	$R_L=300~\Omega,~C_L=35~pF$
			5	ns min	$V_{S1} = V_{S2} = 10 V$; see Figure 30
Charge Injection, Q _{INJ}	310			pC typ	$V_s = 0 V$, $R_s = 0 \Omega$, $C_L = 1 nF$; see Figure 32
Off Isolation	-78			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$; see Figure 26
Channel-to-Channel Crosstalk	-70			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 25

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ADG5412/ADG5413

Parameter	+25°C	–40°C to +85°C	–40°C to +125°C	Unit	Test Conditions/Comments
Total Harmonic Distortion + Noise	0.007			% typ	R _L = 1 kΩ, 20 V p-p, f = 20 Hz to 20 kHz; see Figure 28
–3 dB Bandwidth	160			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 29
Insertion Loss	-0.6			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 29
Cs (Off)	17			pF typ	$V_{s} = 0 V, f = 1 MHz$
C _D (Off)	17			pF typ	$V_{s} = 0 V, f = 1 MHz$
C _D (On), C _s (On)	60			pF typ	$V_{s} = 0 V, f = 1 MHz$
POWER REQUIREMENTS					$V_{DD} = +22 V, V_{SS} = -22 V$
ldd	50			μA typ	Digital inputs = $0 V \text{ or } V_{DD}$
	70		110	µA max	
lss	0.001			μA typ	Digital inputs = $0 V$ or V_{DD}
			1	µA max	
V _{DD} /V _{SS}			±9/±22	V min/V max	GND = 0V

¹ Guaranteed by design; not subject to production test.

12 V SINGLE SUPPLY

 V_{DD} = 12 V \pm 10%, V_{SS} = 0 V, GND = 0 V, unless otherwise noted.

Table 3.

Parameter	+25°C	–40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			0 V to V _{DD}	V	
On Resistance, Ron	19			Ωtyp	$V_s = 0 V$ to 10 V, $I_s = -10 mA$; see Figure 24
	22	27	31	Ωmax	$V_{DD} = 10.8 V, V_{SS} = 0 V$
On-Resistance Match Between Channels, ΔR _{ON}	0.4			Ωtyp	$V_{s} = 0 V$ to 10 V, $I_{s} = -10 \text{ mA}$
	0.8	1	1.2	Ωmax	
On-Resistance Flatness, R _{FLAT (ON)}	4.4			Ωtyp	$V_s = 0 V$ to 10 V, $I_s = -10 mA$
	5.5	6.5	7.5	Ωmax	
LEAKAGE CURRENTS					$V_{DD} = 13.2 V, V_{SS} = 0 V$
Source Off Leakage, Is (Off)	±0.05			nA typ	$V_{s} = 1 \text{ V}/10 \text{ V}, V_{D} = 10 \text{ V}/1 \text{ V};$ see Figure 27
	±0.25	±0.75	±6	nA max	
Drain Off Leakage, I_D (Off)	±0.05			nA typ	$V_{s} = 1 \text{ V}/10 \text{ V}, V_{D} = 10 \text{ V}/1 \text{ V};$ see Figure 27
	±0.25	±0.75	±6	nA max	
Channel On Leakage, I _D (On), I _S (On)	±0.1			nA typ	$V_s = V_D = 1 \text{ V}/10 \text{ V}$; see Figure 23
	±0.4	±2	±12	nA max	
DIGITAL INPUTS					
Input High Voltage, V _{INH}			2.0	V min	
Input Low Voltage, V _{INL}			0.8	V max	
Input Current, I _{INL} or I _{INH}	0.002			μA typ	$V_{IN} = V_{GND} \text{ or } V_{DD}$
			±0.1	μA max	
Digital Input Capacitance, C _{IN}	2.5			pF typ	
DYNAMIC CHARACTERISTICS ¹					
ton	225			ns typ	$R_L=300~\Omega,~C_L=35~pF$
	296	358	403	ns max	$V_s = 8 V$; see Figure 31
toff	150			ns typ	$R_L=300~\Omega,~C_L=35~pF$
	187	222	247	ns max	$V_s = 8 V$; see Figure 31

Parameter	+25°C	–40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
Break-Before-Make Time Delay, t _D (ADG5413 Only)	70			ns typ	$R_L = 300 \ \Omega, \ C_L = 35 \ pF$
			38	ns min	$V_{S1} = V_{S2} = 8 V$; see Figure 30
Charge Injection, Q _{INJ}	95			pC typ	$V_s = 6 V$, $R_s = 0 \Omega$, $C_L = 1 nF$; see Figure 32
Off Isolation	-78			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, f = 100 kHz; see Figure 26
Channel-to-Channel Crosstalk	-70			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 25
Total Harmonic Distortion + Noise	0.07			% typ	$R_L = 1 \text{ k}\Omega$, 6 V p-p, f = 20 Hz to 20 kHz; see Figure 28
-3 dB Bandwidth	180			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 29
Insertion Loss	-1.3			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 29
C _s (Off)	22			pF typ	$V_{s} = 6 V, f = 1 MHz$
C _D (Off)	22			pF typ	$V_s = 6 V, f = 1 MHz$
C _D (On), C _s (On)	58			pF typ	$V_s = 6 V, f = 1 MHz$
POWER REQUIREMENTS					$V_{DD} = 13.2 V$
lod	40			μA typ	Digital inputs = $0 V \text{ or } V_{DD}$
			65	μA max	
V _{DD}			9/40	V min/V max	$GND = 0 V, V_{SS} = 0 V$

¹ Guaranteed by design; not subject to production test.

36 V SINGLE SUPPLY

 V_{DD} = 36 V \pm 10%, V_{SS} = 0 V, GND = 0 V, unless otherwise noted.

Table 4.

Parameter	+25°C	–40°C to +85°C	–40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			$0 V$ to V_{DD}	V	
On Resistance, R _{ON}	10.6			Ωtyp	Vs = 0 V to 30 V, Is = -10 mA; see Figure 24
	12	15	17	Ωmax	$V_{DD} = 32.4 V, V_{SS} = 0 V$
On-Resistance Match Between Channels, ΔR_{ON}	0.35			Ωtyp	$V_s = 0 V$ to 30 V, $I_s = -10 \text{ mA}$
	0.7	0.9	1.1	Ωmax	
On-Resistance Flatness, R _{FLAT(ON)}	2.7			Ωtyp	$V_s = 0 V$ to 30 V, $I_s = -10 mA$
	3.2	3.8	4.5	Ωmax	
LEAKAGE CURRENTS					$V_{DD} = 39.6 V, V_{SS} = 0 V$
Source Off Leakage, Is (Off)	±0.05			nA typ	Vs = 1 V/30 V, V _D = 30 V/1 V; see Figure 27
	±0.25	±0.75	±6	nA max	
Drain Off Leakage, I _D (Off)	±0.05			nA typ	$V_s = 1 V/30 V$, $V_D = 30 V/1 V$; see Figure 27
	±0.25	±0.75	±б	nA max	
Channel On Leakage, I_D (On), I_S (On)	±0.1			nA typ	$V_s = V_D = 1 V/30 V$; see Figure 23
	±0.4	±2	±12	nA max	

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ADG5412/ADG5413

Parameter	+25°C	–40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
DIGITAL INPUTS					
Input High Voltage, V _{INH}			2.0	V min	
Input Low Voltage, VINL			0.8	V max	
Input Current, IINL or IINH	0.002			μA typ	$V_{IN} = V_{GND} \text{ or } V_{DD}$
			±0.1	µA max	
Digital Input Capacitance, C _{IN}	2.5			pF typ	
DYNAMIC CHARACTERISTICS ¹					
ton	180			ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
	220	230	248	ns max	Vs = 18 V; see Figure 31
toff	130			ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
	169	167	174	ns max	Vs = 18 V; see Figure 31
Break-Before-Make Time Delay, t _D (ADG5413 Only)	25			ns typ	$R_L=300~\Omega,~C_L=35~pF$
			8	ns min	$V_{S1} = V_{S2} = 18 V$; see Figure 30
Charge Injection, Q _{INJ}	280			pC typ	$V_s = 18 V$, $R_s = 0 \Omega$, $C_L = 1 nF$; see Figure 32
Off Isolation	-78			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, f = 100 kHz; see Figure 26
Channel-to-Channel Crosstalk	-70			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; Figure 25
Total Harmonic Distortion + Noise	0.03			% typ	$R_L = 1 k\Omega$, 18 V p-p, f = 20 Hz to 20 kHz; see Figure 28
–3 dB Bandwidth	174			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 29
Insertion Loss	-0.8			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 29
Cs (Off)	18			pF typ	$V_{s} = 18 V, f = 1 MHz$
C _D (Off)	18			pF typ	$V_{s} = 18 V, f = 1 MHz$
C _D (On), C _s (On)	58			pF typ	$V_s = 18 V, f = 1 MHz$
POWER REQUIREMENTS					$V_{DD} = 39.6 V$
I _{DD}	80			μA typ	Digital inputs = $0 V \text{ or } V_{DD}$
	100		130	μA max	
V _{DD}			9/40	V min/V max	$GND = 0 V, V_{SS} = 0 V$

¹ Guaranteed by design; not subject to production test.

CONTINUOUS CURRENT PER CHANNEL, Sx OR Dx

Parameter	25°C	85°C	125°C	Unit
CONTINUOUS CURRENT, Sx OR Dx				
$V_{DD} = +15 V, V_{SS} = -15 V$				
TSSOP ($\theta_{JA} = 112.6^{\circ}C/W$)	89	59	37	mA maximum
LFCSP ($\theta_{JA} = 30.4^{\circ}C/W$)	160	94	49	mA maximum
$V_{DD} = +20 V, V_{SS} = -20 V$				
TSSOP ($\theta_{JA} = 112.6^{\circ}C/W$)	95	63	39	mA maximum
LFCSP ($\theta_{JA} = 30.4^{\circ}C/W$)	170	98	50	mA maximum
$V_{DD} = 12 V, V_{SS} = 0 V$				
TSSOP ($\theta_{JA} = 112.6^{\circ}C/W$)	61	43	29	mA maximum
LFCSP ($\theta_{JA} = 30.4^{\circ}C/W$)	110	70	42	mA maximum
$V_{DD} = 36 V, V_{SS} = 0 V$				
TSSOP ($\theta_{JA} = 112.6^{\circ}C/W$)	80	54	35	mA maximum
LFCSP ($\theta_{JA} = 30.4^{\circ}C/W$)	144	87	47	mA maximum

ABSOLUTE MAXIMUM RATINGS

 $T_A = 25^{\circ}$ C, unless otherwise noted.

Table 6.

Parameter	Rating
V _{DD} to V _{SS}	48 V
V _{DD} to GND	–0.3 V to +48 V
Vss to GND	+0.3 V to -48 V
Analog Inputs ¹	V _{SS} – 0.3 V to V _{DD} + 0.3 V or 30 mA, whichever occurs first
Digital Inputs ¹	V _{SS} – 0.3 V to V _{DD} + 0.3 V or 30 mA, whichever occurs first
Peak Current, Sx or Dx Pins	278 mA (pulsed at 1 ms, 10% duty cycle maximum)
Continuous Current, Sx or Dx ²	Data + 15%
Temperature Range	
Operating	–40°C to +125°C
Storage	–65°C to +150°C
Junction Temperature	150°C
Thermal Impedance, θ _{JA}	
16-Lead TSSOP (4-Layer Board)	112.6°C/W
16-Lead LFCSP (4-Layer Board)	30.4°C/W
Reflow Soldering Peak Temperature, Pb Free	260(+0/-5)°C

¹ Overvoltages at the INx, Sx, and Dx pins are clamped by internal diodes. Limit current to the maximum ratings given.

² See Table 5.

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

Only one absolute maximum rating can be applied at any one time.

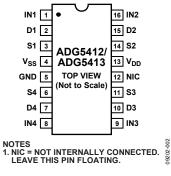
ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

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PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS



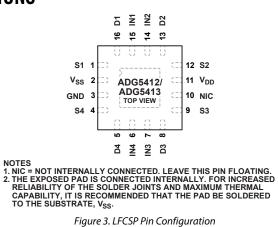


Figure 2. TSSOP Pin Configuration

Table 7. Pin Function Descriptions

Pin No.			
TSSOP	LFCSP	Mnemonic	Description
1	15	IN1	Logic Control Input 1.
2	16	D1	Drain Terminal 1. This pin can be an input or output.
3	1	S1	Source Terminal 1. This pin can be an input or output.
4	2	Vss	Most Negative Power Supply Potential.
5	3	GND	Ground (0 V) Reference.
6	4	S4	Source Terminal 4. This pin can be an input or output.
7	5	D4	Drain Terminal 4. This pin can be an input or output.
8	6	IN4	Logic Control Input 4.
9	7	IN3	Logic Control Input 3.
10	8	D3	Drain Terminal 3. This pin can be an input or output.
11	9	S3	Source Terminal 3. This pin can be an input or output.
12	10	NIC	Not Internally Connected. Leave this pin floating.
13	11	V _{DD}	Most Positive Power Supply Potential.
14	12	S2	Source Terminal 2. This pin can be an input or output.
15	13	D2	Drain Terminal 2. This pin can be an input or output.
16	14	IN2	Logic Control Input 2.
	EP	Exposed Pad	The exposed pad is connected internally. For increased reliability of the solder joints and maximum thermal capability, it is recommended that the pad be soldered to the substrate, V_{SS} .

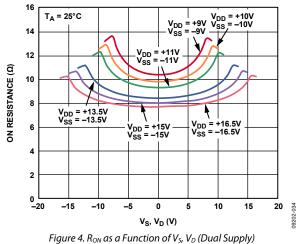
Table 8. ADG5412 Truth Table

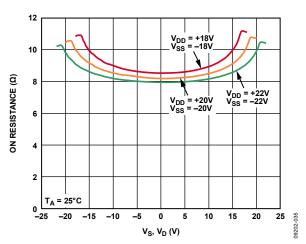
INx	Switch Condition
1	On
0	Off

Table 9. ADG5413 Truth Table

INx	S1, S4	S2, S3
0	Off	On
1	On	Off

TYPICAL PERFORMANCE CHARACTERISTICS







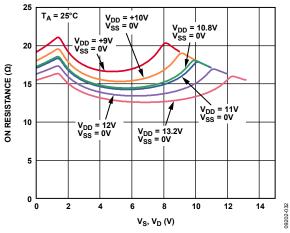


Figure 6. RON as a Function of Vs, VD (Single Supply)

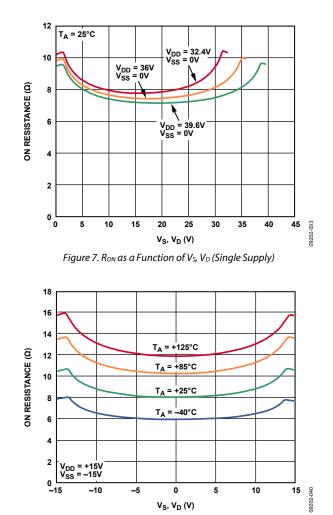


Figure 8. R_{ON} as a Function of V_S (V_D) for Different Temperatures, ±15 V Dual Supply

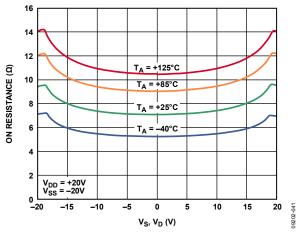


Figure 9. R_{ON} as a Function of V_S (V_D) for Different Temperatures, ± 20 V Dual Supply

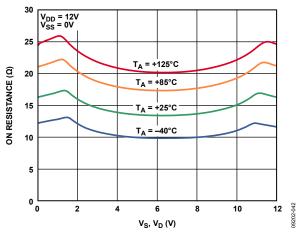
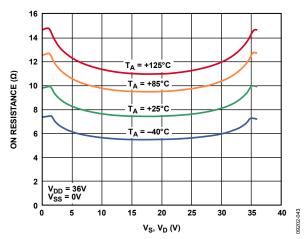
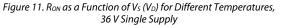


Figure 10. R_{ON} as a Function of V_S (V_D) for Different Temperatures, 12 V Single Supply





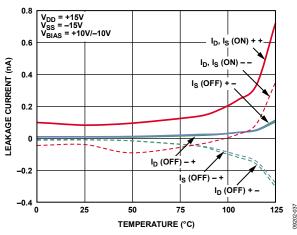


Figure 12. Leakage Currents vs. Temperature, ±15 V Dual Supply

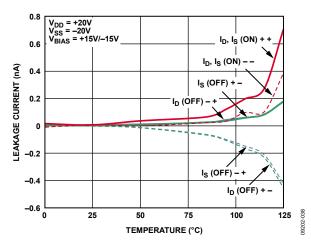
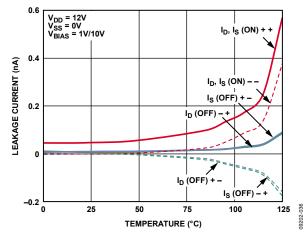


Figure 13. Leakage Currents vs. Temperature, ±20 V Dual Supply





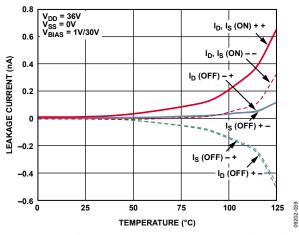


Figure 15. Leakage Currents vs. Temperature, 36 V Single Supply

10M 09202-026

09202-027

20

1G 9202-029

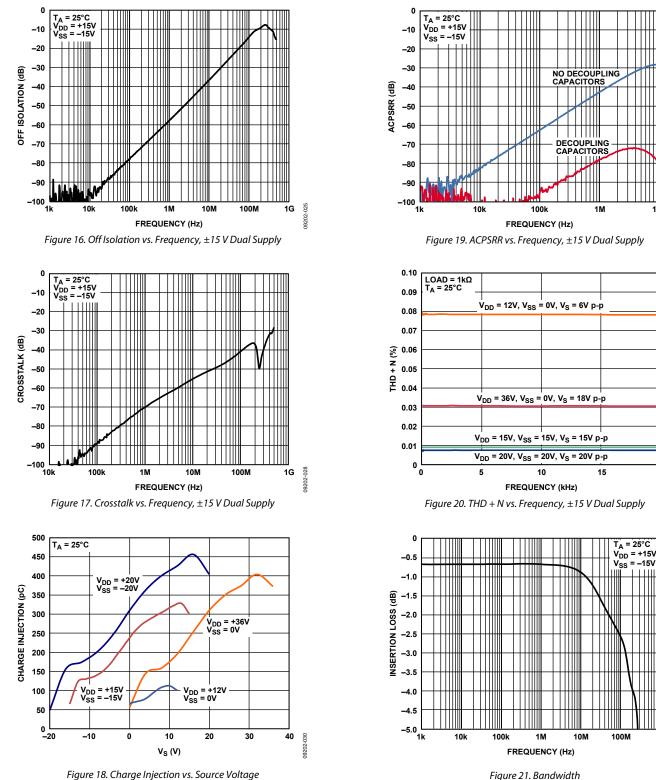


Figure 21. Bandwidth

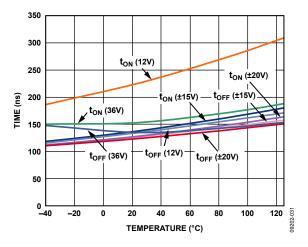


Figure 22. ton, toFF Times vs. Temperature

ID (OFF)

09202-015

AUDIO PRECISION

V p-i

NETWORK ANALYZER

٧s

ウ о v_{out}

09202-023

50Ω

VOUT WITH SWITCH

R_L 50Ω

9202-024

Rs

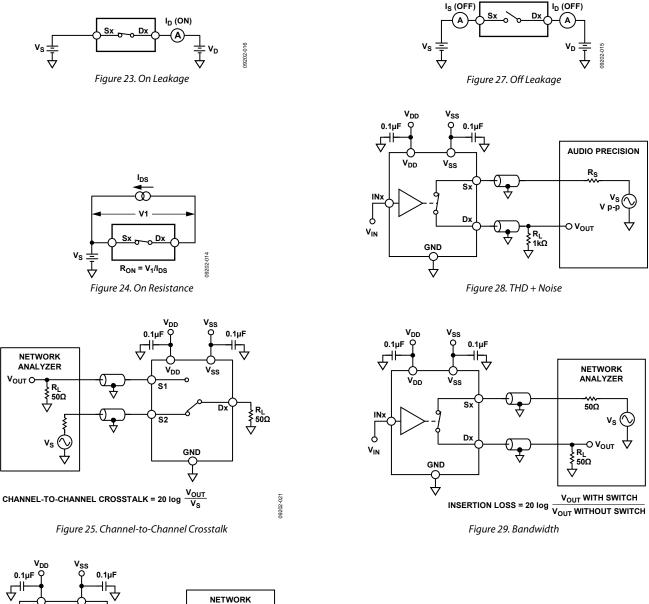
-O V_{OUT}

 $\stackrel{\{\overline{R_L}\\{}^{1k\Omega}}{\bigtriangledown}$

€

•

TEST CIRCUITS



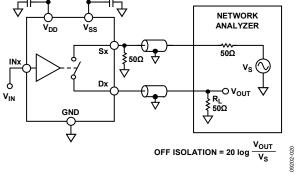


Figure 26. Off Isolation

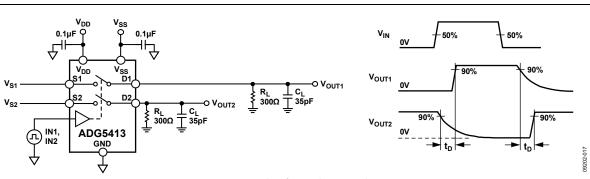


Figure 30. Break-Before-Make Time Delay, t_D

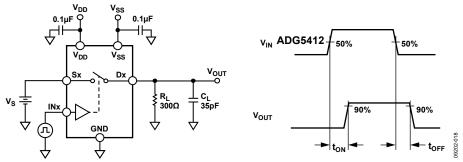
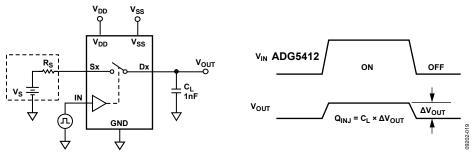
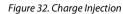


Figure 31. Switching Times





TERMINOLOGY

\mathbf{I}_{DD}

 $I_{\rm DD}$ represents the positive supply current.

Iss

Iss represents the negative supply current.

VD, Vs

 $V_{\rm D}$ and $V_{\rm S}$ represent the analog voltage on Terminal D and Terminal S, respectively.

Ron

 $R_{\mbox{\scriptsize ON}}$ represents the ohmic resistance between Terminal D and Terminal S.

ΔR_{ON}

 $\Delta R_{\rm ON}$ represents the difference between the $R_{\rm ON}$ of any two channels.

$R_{\rm FLAT\ (ON)}$

Flatness that is defined as the difference between the maximum and minimum value of on resistance measured over the specified analog signal range is represented by $R_{FLAT (ON)}$.

Is (Off)

 $I_{\text{S}}\left(\text{Off}\right)$ is the source leakage current with the switch off.

I_D (Off)

 $I_{\rm D}\left(Off\right)$ is the drain leakage current with the switch off.

I_{D} (On), I_{S} (On)

 $I_{\rm D}$ (On) and $I_{\rm S}$ (On) represent the channel leakage currents with the switch on.

VINL

 $V_{\mbox{\scriptsize INL}}$ is the maximum input voltage for Logic 0.

VINH

 $V_{\mbox{\scriptsize INH}}$ is the minimum input voltage for Logic 1.

$I_{\rm INL}, I_{\rm INH}$

 $I_{\rm INL}$ and $I_{\rm INH}$ represent the low and high input currents of the digital inputs.

C_D (Off)

 C_D (Off) represents the off switch drain capacitance, which is measured with reference to ground.

Cs (Off)

C_s (Off) represents the off switch source capacitance, which is measured with reference to ground.

C_D (On), C_S (On)

 C_D (On) and C_S (On) represent on switch capacitances, which are measured with reference to ground.

CIN

C_{IN} is the digital input capacitance.

ton

 $t_{\rm ON}$ represents the delay between applying the digital control input and the output switching on.

toff

 $t_{\mbox{\scriptsize OFF}}$ represents the delay between applying the digital control input and the output switching off.

t_D

 $t_{\rm D}$ represents the off time measured between the 80% point of both switches when switching from one address state to another.

Off Isolation

Off isolation is a measure of unwanted signal coupling through an off switch.

Charge Injection

Charge injection is a measure of the glitch impulse transferred from the digital input to the analog output during switching.

Crosstalk

Crosstalk is a measure of unwanted signal that is coupled through from one channel to another as a result of parasitic capacitance.

Bandwidth

Bandwidth is the frequency at which the output is attenuated by 3 dB.

On Response

On response is the frequency response of the on switch.

Insertion Loss

Insertion loss is the loss due to the on resistance of the switch.

Total Harmonic Distortion + Noise (THD + N)

The ratio of the harmonic amplitude plus noise of the signal to the fundamental is represented by THD + N.

AC Power Supply Rejection Ratio (ACPSRR)

ACPSRR is the ratio of the amplitude of signal on the output to the amplitude of the modulation. This is a measure of the ability of the part to avoid coupling noise and spurious signals that appear on the supply voltage pin to the output of the switch. The dc voltage on the device is modulated by a sine wave of 0.62 V p-p.

TRENCH ISOLATION

In the ADG5412 and ADG5413, an insulating oxide layer (trench) is placed between the NMOS and the PMOS transistors of each CMOS switch. Parasitic junctions, which occur between the transistors in junction isolated switches, are eliminated, and the result is a completely latch-up proof switch.

In junction isolation, the N and P wells of the PMOS and NMOS transistors form a diode that is reverse-biased under normal operation. However, during overvoltage conditions, this diode can become forward-biased. A silicon controlled rectifier (SCR) type circuit is formed by the two transistors causing a significant amplification of the current that, in turn, leads to latch-up. With trench isolation, this diode is removed, and the result is a latch-up proof switch.

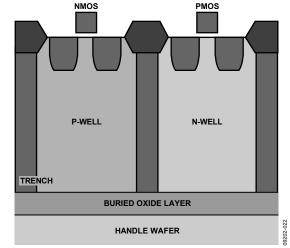
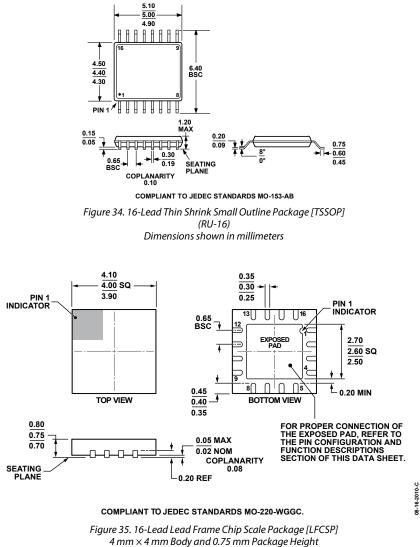


Figure 33. Trench Isolation

APPLICATIONS INFORMATION

The high voltage latch-up proof family of switches and multiplexers provide a robust solution for instrumentation, industrial, automotive, aerospace, and other harsh environments that are prone to latch-up, which is an undesirable high current state that can lead to device failure and persists until the power supply is turned off. The ADG5412/ADG5413 high voltage switches allow single-supply operation from 9 V to 40 V and dual-supply operation from \pm 9 V to \pm 22 V. The ADG5412/ADG5413 (as well as other select devices within the same family) achieve an 8 kV human body model ESD rating, which provides a robust solution eliminating the need for separate protect circuitry designs in some applications.

OUTLINE DIMENSIONS



(CP-16-17) Dimensions shown in millimeters

ORDERING GUIDE

Model ^{1,2}	Temperature Range	Package Description	Package Option
ADG5412BRUZ	-40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG5412BRUZ-REEL7	-40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG5412BCPZ-REEL7	-40°C to +125°C	16-Lead Lead Frame Chip Scale Package [LFCSP]	CP-16-17
ADG5413BRUZ	-40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG5413BRUZ-REEL7	-40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG5413BCPZ-REEL7	-40°C to +125°C	16-Lead Lead Frame Chip Scale Package [LFCSP]	CP-16-17
EVAL-16TSSOPEBZ		Evaluation Board	

 1 Z = RoHS Compliant Part.

² The EVAL-16TSSOPEBZ can be used to test the ADG5412 and the ADG5413.

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ADG5413BRUZ ADG5412BRUZ-REEL7 ADG5412BRUZ ADG5413BRUZ-REEL7 ADG5412WBCPZ-REEL7 ADG5412BCPZ-REEL7 EVAL-16TSSOPEBZ ADG5413BCPZ-REEL7